

Power Transistor (-80V, -1A)

2SB1260 / 2SB1181 / 2SB1241

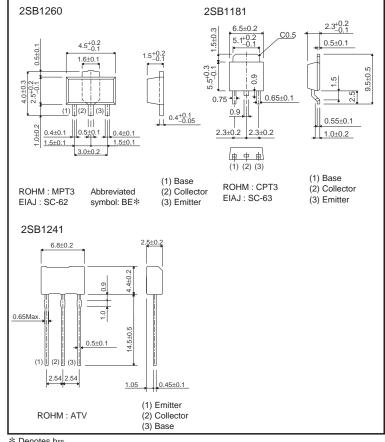
Features

- 1) Hight breakdown voltage and high current.
- $BV_{CEO} = -80V$, $I_C = -1A$
- 2) Good hee linearty.
- 3) Low VCE(sat).

Complements the 2SD1898 / 2SD1863 / 2SD1733.

 Structure Epitaxial planar type PNP silicon transistor

•Dimensions (Unit : mm)



* Denotes hre

●Absolute maximum ratings (Ta=25°C)

Par	ameter	Symbol	Limits	Unit
Collector-base v	oltage	Vсво	-80	V
Collector-emitter	voltage	Vceo	-80	V
Emitter-base vol	tage	Vebo	-5	V
Collector ourrent		lc	-1	A (DC)
Collector current		Іср	-2 *1	A (Pulse)
	2SB1260		0.5	
Collector power	2581200	D-	2 *2	W
dissipation	2SB1241, 2SB1181	Pc	1 * ³	
	2SB1181		10	W (Tc=25°C)
Junction tempera	ature	Tj	150	°C
Storage tempera	ture	Tstg	-55 to 150	°C

*1 2SB1260 : Pw=20ms duty=1/2

2SB1241 : Single pulse, Pw=100ms

*2 2SB1260 : When mounted on a 40×40×0.7 mm ceramic board.

*3 2SB1241 : Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

●Electrical characteristics (Ta=25°C)

Param	eter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base break	down voltage	ВУсво	-80	-	-	V	Ic=-50μA
Collector-emitter brea	akdown voltage	BVCEO	-80	-	-	V	Ic=-1mA
Emitter-base breakdo	own voltage	ВVево	-5	-	-	V	Iε=-50μA
Collector cutoff curre	nt	Ісво	_	_	-1	μΑ	Vcb=-60V
Emitter cutoff current		Іево	-	-	-1	μΑ	VEB=-4V
Collector-emitter satu	ration voltage	VCE(sat)	-	-	-0.4	V	Ic/I _B = -500mA/ -50mA
DC current transfer ratio	2SB1260, 2SB1181	hfe	120	-	390	-	Vce= -3V. lc= -0.1A
	2SB1241		120	-	390	_	$VC_{E} = -3V, IC = -0.1A$
Transition frequency	2SB1181	f⊤	-	100	-	MHz	Vce=-10V, Ie=50mA, f=100MHz
Output capacitance	2SB1260	Cob	_	20	_	pF	Vcb= -10V IE=0A
	2SB1181, 2SB1241	000	_	25	_	pF	f=1MHz

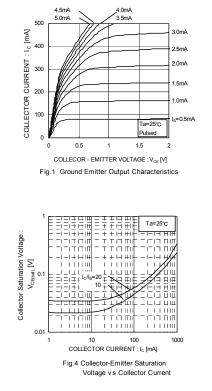
Packaging specifications and hfe

		Package		Taping	
		Code	TL	TV2	T100
Туре	hfe	Basic ordering unit (pieces)	2500	2500	1000
2SB1260	QR		-	_	0
2SB1241	QR		_	0	_
2SB1181	QR		0	_	_

hFE values are classified as follows :

Item	Q	R
hfe	120 to 270	180 to 390

•Electrical characteristic curves



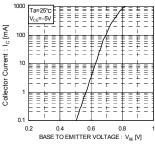
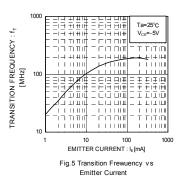


Fig.2 Grounded Emitter Propagation Characteristics



DC CURRENT GAIN : hFE	1000	
		1 10 100 1000
		COLLECTOR CURRENT : Ic [mA]

Fig.3 DC Current Gain vs Collector Current

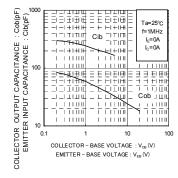


Fig.6 Emitter Input Capacitance vs. Emitter-Base Voltage Collector Output Capacitance vs. Collector-Base

	Notes
	ng or reproduction of this document, in part or in whole, is permitted without the f ROHM Co.,Ltd.
The conte	nt specified herein is subject to change for improvement without notice.
"Products	nt specified herein is for the purpose of introducing ROHM's products (hereinafte "). If you wish to use any such Product, please be sure to refer to the specifications be obtained from ROHM upon request.
illustrate t	of application circuits, circuit constants and any other information contained herein he standard usage and operations of the Products. The peripheral conditions mus nto account when designing circuits for mass production.
However,	e was taken in ensuring the accuracy of the information specified in this document should you incur any damage arising from any inaccuracy or misprint of sucl n, ROHM shall bear no responsibility for such damage.
examples implicitly, other part	ical information specified herein is intended only to show the typical functions of and of application circuits for the Products. ROHM does not grant you, explicitly o any license to use or exercise intellectual property or other rights held by ROHM and ies. ROHM shall bear no responsibility whatsoever for any dispute arising from the h technical information.
equipmen	icts specified in this document are intended to be used with general-use electronic t or devices (such as audio visual equipment, office-automation equipment, commu evices, electronic appliances and amusement devices).
The Produ	cts specified in this document are not designed to be radiation tolerant.
	HM always makes efforts to enhance the quality and reliability of its Products, a ay fail or malfunction for a variety of reasons.
against th failure of a shall bear	sure to implement in your equipment using the Products safety measures to guard e possibility of physical injury, fire or any other damage caused in the event of the any Product, such as derating, redundancy, fire control and fail-safe designs. ROHM no responsibility whatsoever for your use of any Product outside of the prescribed not in accordance with the instruction manual.
system wi may resul instrumen fuel-contr any of the	acts are not designed or manufactured to be used with any equipment, device on hich requires an extremely high level of reliability the failure or malfunction of which t in a direct threat to human life or create a risk of human injury (such as a medica t, transportation equipment, aerospace machinery, nuclear-reactor controller oller or other safety device). ROHM shall bear no responsibility in any way for use o Products for the above special purposes. If a Product is intended to be used for an ial purpose, please contact a ROHM sales representative before purchasing.
be contro	nd to export or ship overseas any Product or technology specified herein that may led under the Foreign Exchange and the Foreign Trade Law, you will be required to cense or permit under the Law.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/